



# **ELECTRONIC SYSTEM**

**AMPLIFIER**

**GADAFI OMAR**

# **ELECTRONIC SYSTEM**

## **AMPLIFIER**



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**Writer**

Gadaffi bin Omar

**Published in 2021**

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Perpustakaan Negara Malaysia

Cataloguing-in-Publication Data

Gadaffi Omar

ELECTRONIC SYSTEM : AMPLIFIER / GADAFFI OMAR.

Mode of access: Internet

eISBN 978-967-2241-89-8

1. Amplifiers (Electronics).
2. Electronics.
3. Government publications--Malaysia.
4. Electronic books.

I. Title.

621.381535

**Published by:**

Politeknik Merlimau, Melaka

KB1031 Pej Pos Merlimau,

77300 Merlimau Melaka

## **PREFACE**

This books aims for students of mechatronic engineering with the explanation of the basic concepts of semiconductor devices to diode, transistor, Common emitter, biased voltage divider, collector amplifier, and Common base.

The entire book is written in a simple way to enable them to students understand the concepts quickly and the subject in easy way. This book shall provide knowledge on the theory, concept and application of formula and to acquire the problem solving skills related to the respective processes.

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# AMPLIFIER

# AMPLIFIER

COMMON BASE AMPLIFIER  
COMMON COLLECTOR AMPLIFIER  
COMMON EMITTER AMPLIFIER  
LOAD LINE

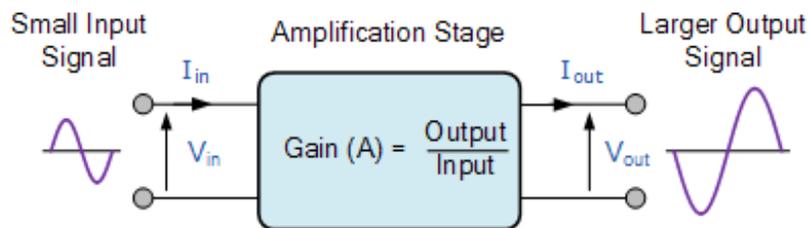
# INTRODUCTION

- **WHAT IS AMPLIFIER?**

- An electronic device that increases the power of a signal.
- Amplifiers is a circuit that contains the amplifying device, such as a **Transistor**, Field Effect Transistor or Op-amp, with the output signal being much greater than that of the input signal.

- **AMPLIFIER GAIN**

- Amplifier gain is simply the ratio of the output divided-by the input.



- There are three different kinds of amplifier gain which can be measured;
  - Voltage Gain ( $A_v$ ),
  - Current Gain ( $A_i$ )
  - Power Gain ( $A_p$ )

# INTRODUCTION

- **VOLTAGE GAIN**

- *Voltage Gain* ( $A_V$ ) =  $\frac{\text{Output Voltage}}{\text{Input Voltage}} = \frac{V_{out}}{V_{in}}$

- **CURRENT GAIN**

- *Current Gain* ( $A_i$ ) =  $\frac{\text{Output Current}}{\text{Input Current}} = \frac{I_{out}}{I_{in}}$

- **POWER GAIN**

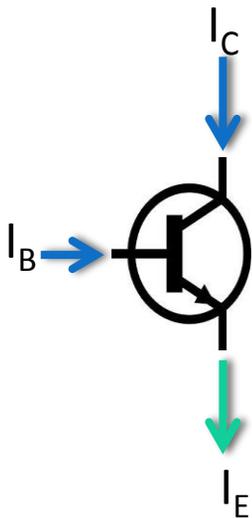
- *Power Gain* ( $A_p$ ) =  $\frac{\text{Output Power}}{\text{Input Power}} = \frac{P_{out}}{P_{in}}$

- Common Amplifier devices;

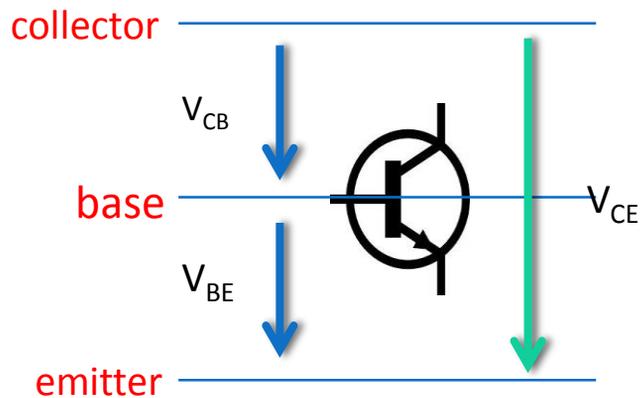
- Hi-fi or home theater unit
  - In car entertainment - (radio → AMPLIFIER → sub woofer/speaker)

# INTRODUCTION

- TRANSISTOR BASIC FORMULA (Kirchoff Current Law and Kirchoff Voltage Law)



$$I_E = I_B + I_C$$



$$V_{CE} = V_{CB} + V_{BE}$$

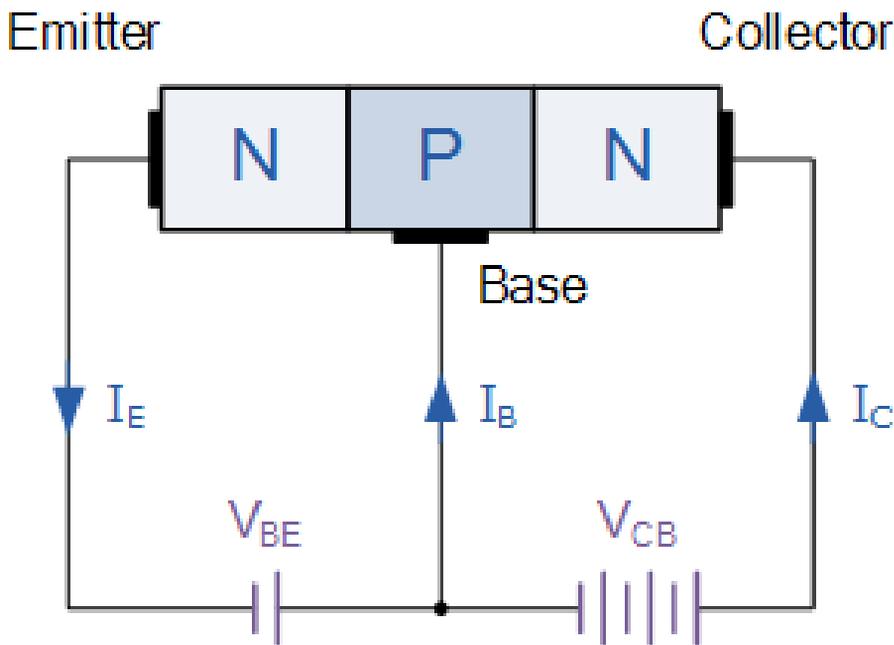
$$V_{BE} = 0.7V \text{ (silicon)}$$

$$V_{BE} = 0.3V \text{ (germanium)}$$

$$V_{BE} = 0V \text{ (if not stated in question)}$$

# INTRODUCTION

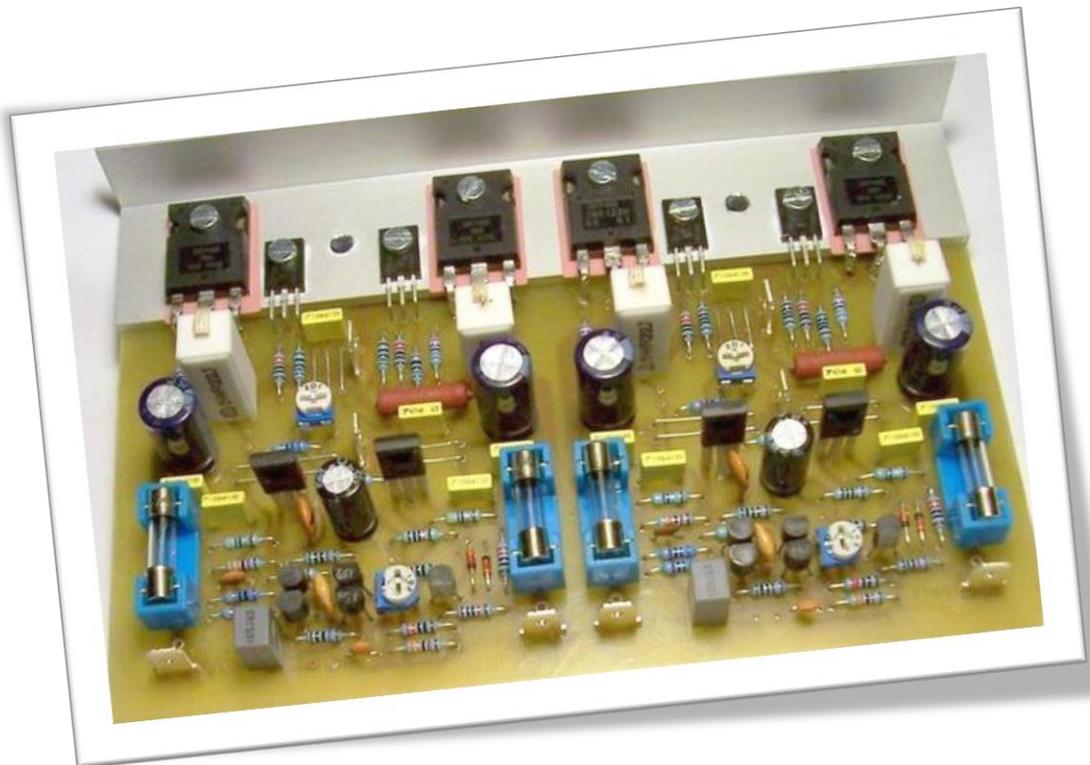
- CONDITIONS FOR TRANSISTOR TO OPERATE



- Pin EB (Emitter Base) – **Forward Biased**  
( +ve battery connect to P material while -ve battery connect to N material)
- Pin CB (Collector Base) – **Reverse Biased**  
( -ve battery connect to P material while +ve battery connect to N material)

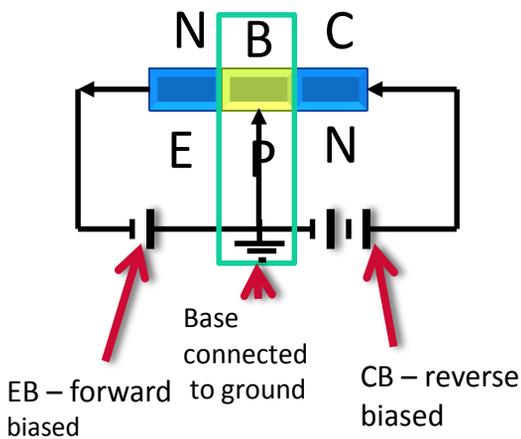
# TRANSISTOR AS AMPLIFIER

- There are THREE configuration for transistor to operate as amplifier;
  - Common Base
  - Common Collector
  - Common Emitter

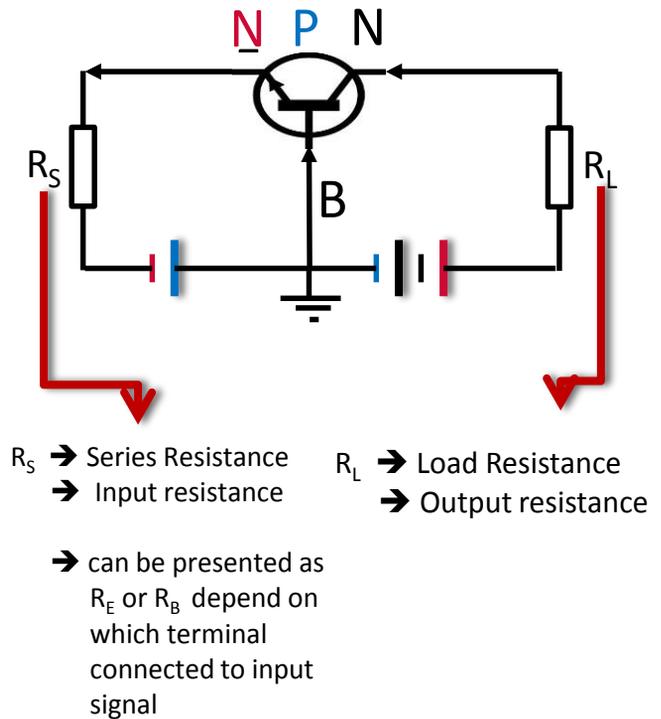


# COMMON BASE AMPLIFIER

- BATTERY CONNECTION

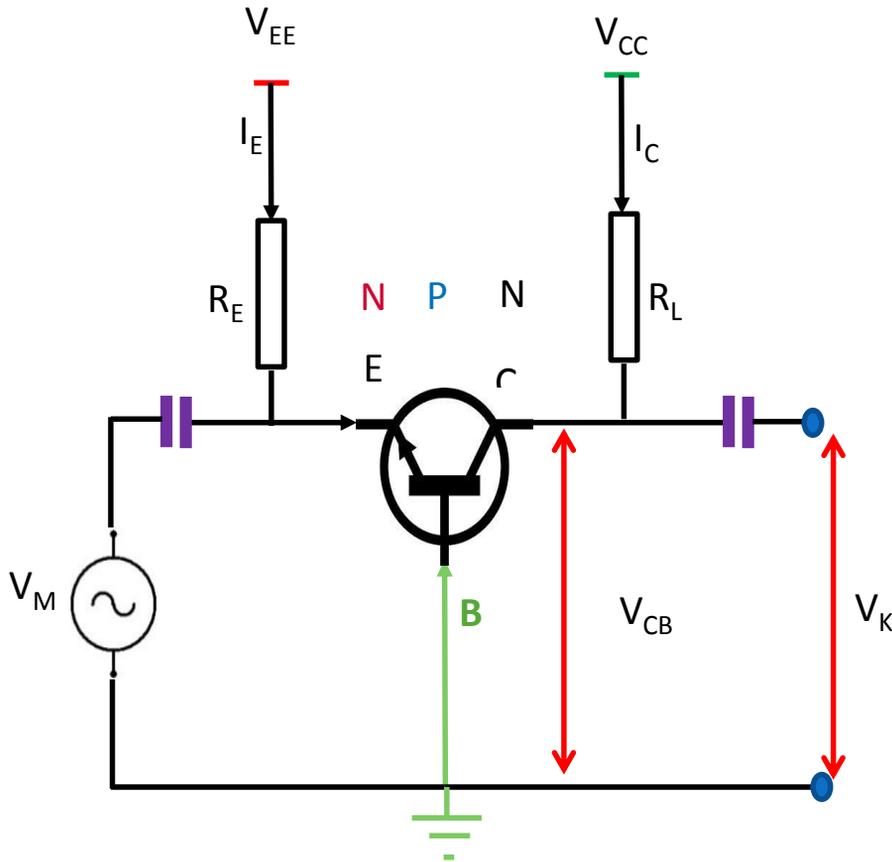


- COMMON BASE AMPLIFIER CIRCUIT



# COMMON BASE AMPLIFIER

- COMMON BASE AMPLIFIER CIRCUIT WITH INPUT SIGNAL



$$R_L = R_C$$

$I_B$  is so small

thus  $I_E = I_C$

$$V_K = V_{CB}$$

## INPUT

$$V_{EE} = V_{RE} + V_{BE}$$

$$V_{EE} = I_E R_E + V_{BE}$$

$$I_E = \frac{V_{EE} - V_{BE}}{R_E}$$

## OUTPUT

$$V_{CC} = V_{RL} + V_K$$

$$V_{CC} = I_C R_L + V_K$$

$$V_K = V_{CC} - I_C R_L$$

$$I_E = I_C$$

# COMMON BASE AMPLIFIER

- **Alpha ( $\alpha$ )** is a current gain factor for common base amplifier.
- It can be divided into two condition;

*i.* 
$$\alpha_{DC} = \frac{I_C}{I_E}$$

- current gain when collector current, emitter current and  $V_K$  at a fixed value.

*ii.* 
$$\alpha_{AC} = \frac{\Delta I_C}{\Delta I_E}$$

- current gain when there is a changed of values for collector current and emitter current while  $V_K$  at a fixed value.

\*\*  $V_K$  = output voltage

# COMMON BASE AMPLIFIER GAIN CALCULATION (E.G. 1)

- Calculate the value of  $\alpha_{DC}$  and  $\alpha_{AC}$  if given the initial value of collector current ( $I_C$ ) is 0.98mA, while the emitter current ( $I_E$ ) is 1mA. Then the value of both current rise to 1mA (for  $I_C$ ) and 1.05mA (for  $I_E$ )
- **SOLUTION**

$$\alpha_{DC} = \frac{I_C}{I_E}$$

$$\alpha_{DC} = \frac{0.95 \text{ mA}}{1 \text{ mA}}$$

$$\alpha_{DC} = \mathbf{0.98}$$

$$\alpha_{AC} = \frac{\Delta I_C}{\Delta I_E}$$

$$\alpha_{AC} = \frac{1 \text{ mA} - 0.95 \text{ mA}}{1.05 \text{ mA} - 1 \text{ mA}}$$

$$\alpha_{AC} = \mathbf{0.4}$$

# COMMON BASE AMPLIFIER

## Common Base Amplifier Characteristic

Input resistance ( $R_{in}$ )	Low
Output resistance ( $R_{out}$ )	High
Current gain ( $A_i$ )	No
Voltage gain ( $A_v$ )	High
Power gain ( $A_p$ )	High
Phase shift	No

- $A_i = \frac{I_C}{I_E} I_C \leq I_E$   
 $A_i \leq 1$ , thus there is **no current gain**

- $A_v = \frac{V_{CB}}{V_{EB}} V_{CE} = V_{CB} + V_{BE}$

$$V_{BE} = V_{CE} - V_{CB}$$

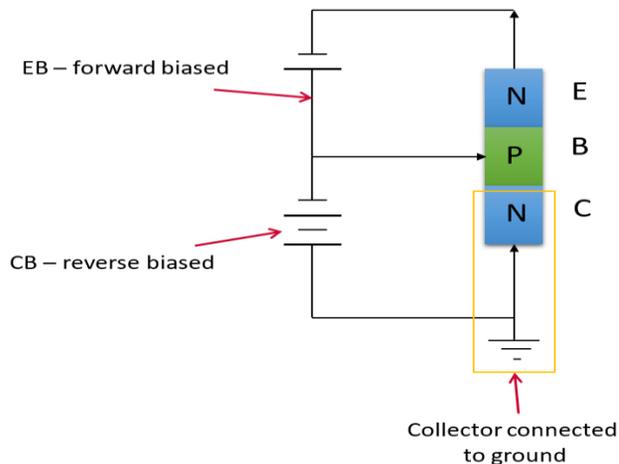
$$V_{EB} = V_{CB} - V_{CE}$$

So  $A_v = \frac{V_{CB}}{V_{CB} - V_{CE}} \frac{\text{big value}}{\text{small value}}$

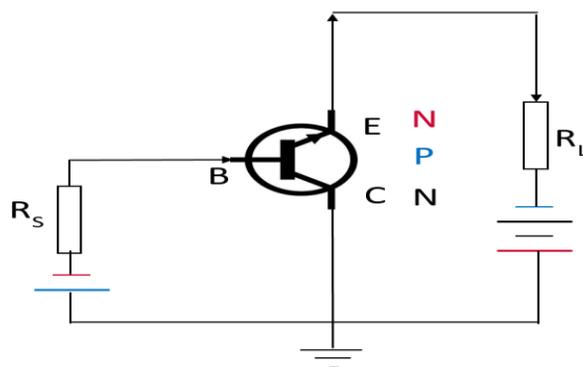
- Thus **Voltage gain ( $A_v$ ) is high.**
- $A_p$  refer to  $A_v$ , thus **Ap is also high**
- EB is forward biased by  $V_{BB}$ , thus **input resistance value is small**
- CB is reverse biased by  $V_{CC}$ , thus **output resistance value is high.**

# COMMON COLLECTOR AMPLIFIER

- BATTERY CONNECTION



- COMMON COLLECTOR AMPLIFIER CIRCUIT

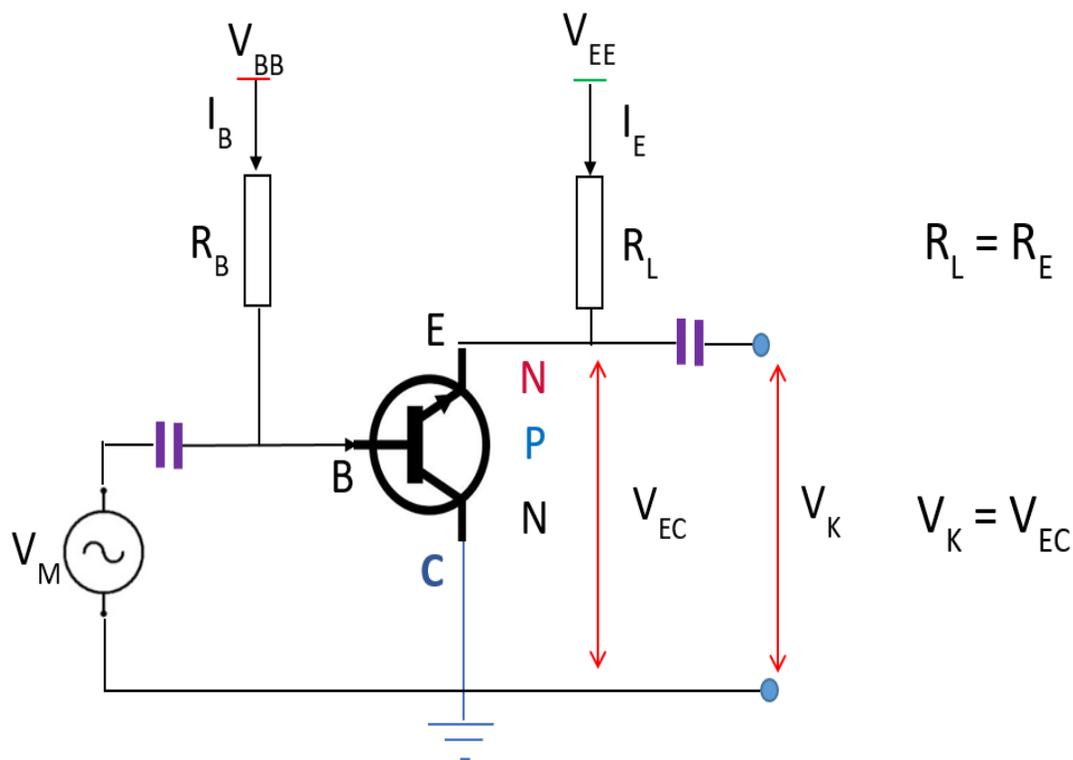


$R_s$  → Series Resistance  
 → Input resistance  
 → can be presented as  $R_B$

$R_L$  → Load Resistance  
 → Output resistance

# COMMON COLLECTOR AMPLIFIER

- COMMON COLLECTOR AMPLIFIER CIRCUIT WITH INPUT SIGNAL



# COMMON COLLECTOR AMPLIFIER

## Common Collector Amplifier Characteristic

Input resistance ( $R_{in}$ )	High
Output resistance ( $R_{out}$ )	Low
Current gain ( $A_i$ )	High
Voltage gain ( $A_v$ )	Low
Power gain ( $A_p$ )	Low
Phase shift	No

- $A_i = \frac{I_E \text{ big value}}{I_B \text{ small value}}$  thus  $A_i$  is high

- $A_v = \frac{V_{EC}}{V_{BC}} V_{EC} = V_{BC} + V_{EB}$

$V_{EB}$  value is small

- $V_{BC} \leq V_{EC}$

So  $A_v = \frac{V_{EC} \text{ bigger value}}{V_{BC} \text{ big value}}$

- Thus **Voltage gain ( $A_v$ ) is LOW.**

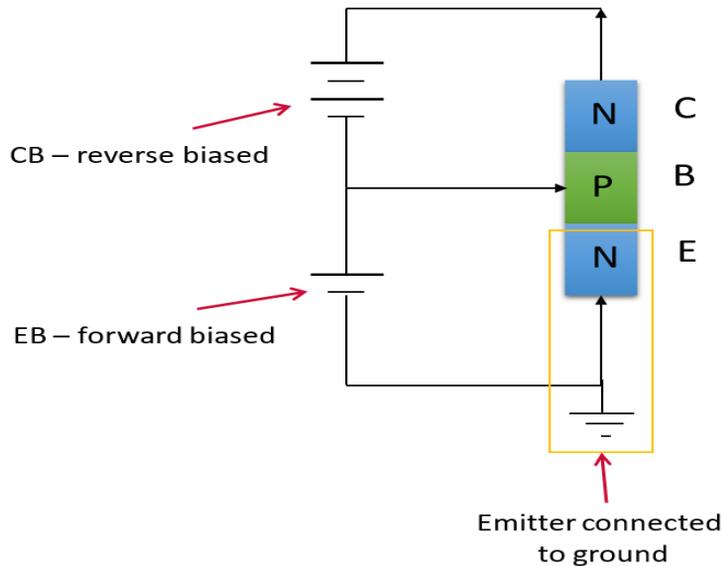
- $A_p$  refer to  $A_v$ , thus  **$A_p$  is also LOW**

- EB is forward biased by  $(V_{EE} - V_{BB})$ , thus **input resistance value is HIGH**

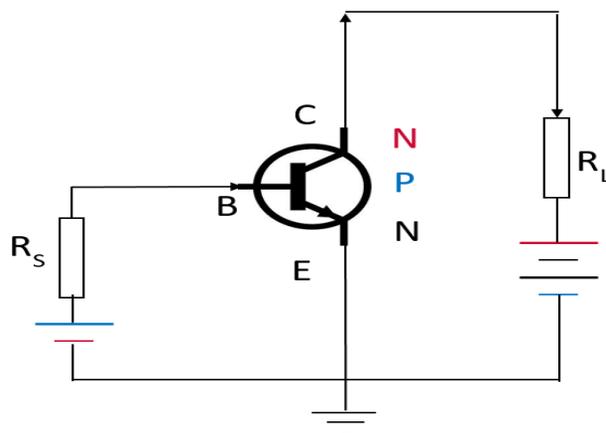
- CB is reverse biased by  $V_{BB}$ , thus **output resistance value is LOW.**

# COMMON EMITTER AMPLIFIER

- BATTERY CONNECTION



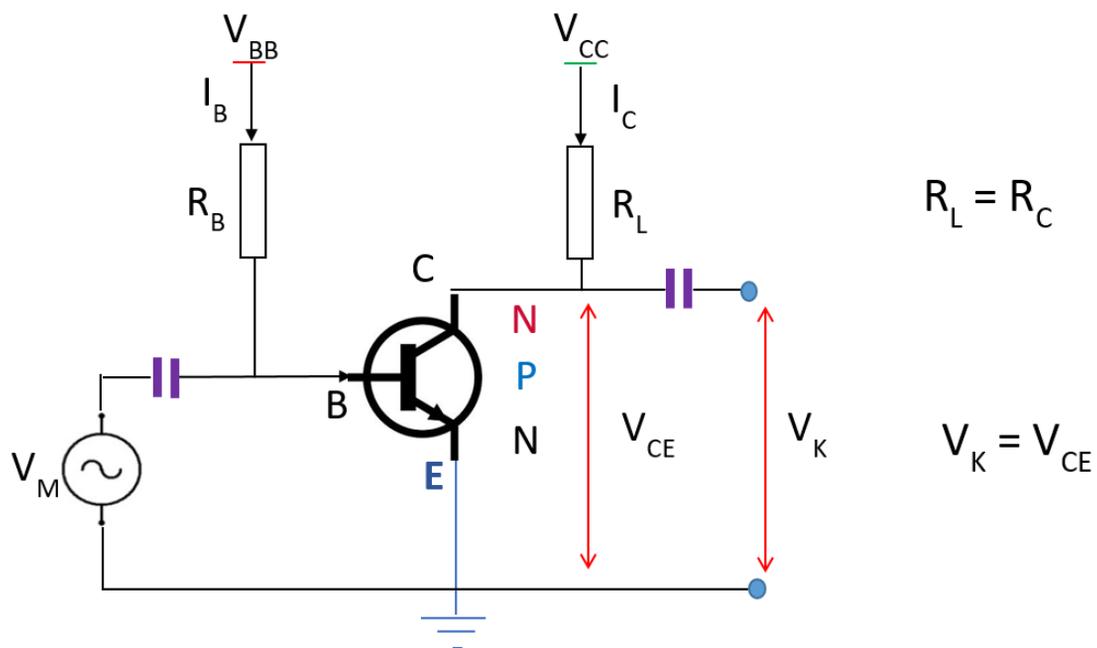
- COMMON EMITTER AMPLIFIER CIRCUIT



- |                             |                         |
|-----------------------------|-------------------------|
| $R_S$ → Series Resistance   | $R_L$ → Load Resistance |
| → Input resistance          | → Output resistance     |
| → can be presented as $R_B$ |                         |

# COMMON EMITTER AMPLIFIER

- COMMON EMITTER AMPLIFIER CIRCUIT WITH INPUT SIGNAL



## INPUT

$$V_{BB} = V_{RB} + V_{BE}$$

$$V_{BB} = I_B R_B + V_{BE}$$

$$I_B = \frac{V_{BB} - V_{BE}}{R_B}$$

## OUTPUT

$$I_C = \beta \cdot I_B$$

$$V_{CC} = V_{RL} + V_K$$

$$V_{CC} = I_C R_L + V_K$$

$$V_K = V_{CC} - I_C R_L$$

# COMMON EMITTER AMPLIFIER

- **Beta ( $\beta$ )** is a current gain factor for common emitter amplifier.
- It can be divided into two condition;

*i.* 
$$\beta_{DC} = \frac{I_C}{I_B}$$

- current gain when collector current, base current and  $V_K$  at a fixed value.

*ii.* 
$$\beta_{AC} = \frac{\Delta I_C}{\Delta I_B}$$

- current gain when there is a changed of values for collector current and base current while  $V_K$  at a fixed value.

$V_K$  also can be represented or written as  $V_C$

# COMMON EMITTER AMPLIFIER

## Common Emitter Amplifier Characteristic

Input resistance ( $R_{in}$ )	Low
Output resistance ( $R_{out}$ )	High
Current gain ( $A_i$ )	High
Voltage gain ( $A_v$ )	High
Power gain ( $A_p$ )	High
Phase shift	$180^\circ$

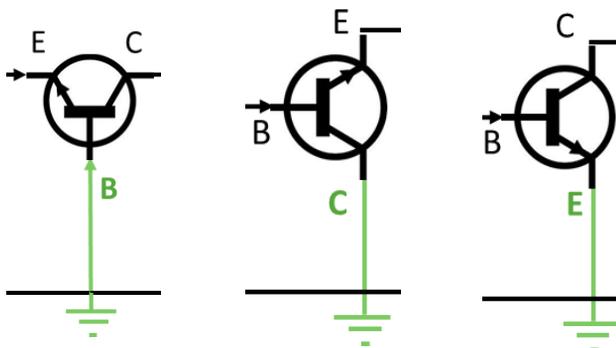
- $A_i = \frac{I_C \text{ big value}}{I_B \text{ small value}}$  thus  $A_i$  is **HIGH**
- $A_v = \frac{V_{CE}}{V_{BE}} V_{CE} = V_{CB} + V_{BE}$   
 $V_{BE}$  value is small  
So  $A_v = \frac{V_{CE} \text{ big value}}{V_{CB} \text{ small value}}$
- Thus **Voltage gain ( $A_v$ ) is HIGH.**
- $A_p$  refer to  $A_v$ , thus  **$A_p$  is also HIGH**
- EB is forward biased by ( $V_{BB}$ ), thus **input resistance value is LOW**
- CB is reverse biased by  $V_{CC}$ , thus **output resistance value is HIGH.**

# AMPLIFIER SUMMARY

## Differentiation between amplifier characteristic

Amplifier Characteristic	Common Base	Common Collector	Common Emitter
Input resistance ( $R_{in}$ )	Low	High	Low
Output resistance ( $R_{out}$ )	High	Low	High
Current gain ( $A_i$ )	No	High	High
Voltage gain ( $A_v$ )	High	Low	High
Power gain ( $A_p$ )	High	Low	High
Phase shift	No	No	180°

- **Tips to identify types of amplifier**
  - LOOK AT WHICH TRANSISTOR PIN IS GROUNDED



## Tips to SOLVE basic amplifier calculation

### STEP 1 : Derive Input formula

$$V_{EE} = V_{RE} + V_{BE} \text{ (Common Base)}$$

$$V_{BB} = V_{RB} + V_{BE} \text{ (Common Emitter)}$$

### STEP 2 : Determine $V_{BE}$

silicon = 0.7V , germanium = 0.3V @  
not mention/none = 0V

### STEP 3 : Determine Input Current

$$I_C \text{ (Common Base) @}$$

$$I_B \text{ (Common Emitter)}$$

### STEP 4 : Determine Output Current

$$I_E = I_C \text{ (Common Base) @}$$

$$I_C = \beta \cdot I_B \text{ (Common Emitter)}$$

### STEP 5 : Derive Output Formula

$$V_{CC} = V_{RL} + V_{CB} \text{ (Common Base)}$$

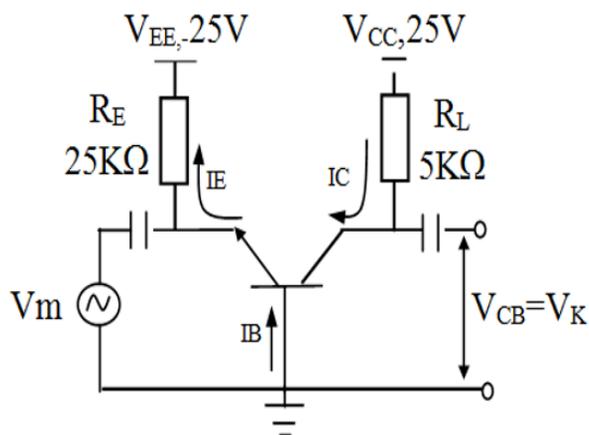
$$V_{CC} = V_{RL} + V_{CE} \text{ (Common Emitter)}$$

### STEP 6 : Determine Output Voltage

$$V_K = V_{CB} \text{ (Common Base)}$$

$$V_K = V_{CE} \text{ (Common Emitter)}$$

# COMMON BASE AMPLIFIER CALCULATION (E.G. 1)



- Determine the output voltage for common base amplifier above

## SOLUTION

Given;

$$R_E = 25 \text{ K}\Omega, \quad R_L = 5 \text{ K}\Omega,$$

$$V_{EE} = 25\text{V}, \quad V_{CC} = 25\text{V}, \quad V_{BE} = 0\text{V}$$

$$V_{EE} = V_{RE} + V_{BE}$$

$$V_{EE} = I_E R_E + V_{BE}$$

$$I_E = \frac{V_{EE}}{R_E} = \frac{25\text{V}}{25\text{K}\Omega} = \underline{1\text{mA}}$$

$$I_C = I_E = \underline{1\text{mA}}$$

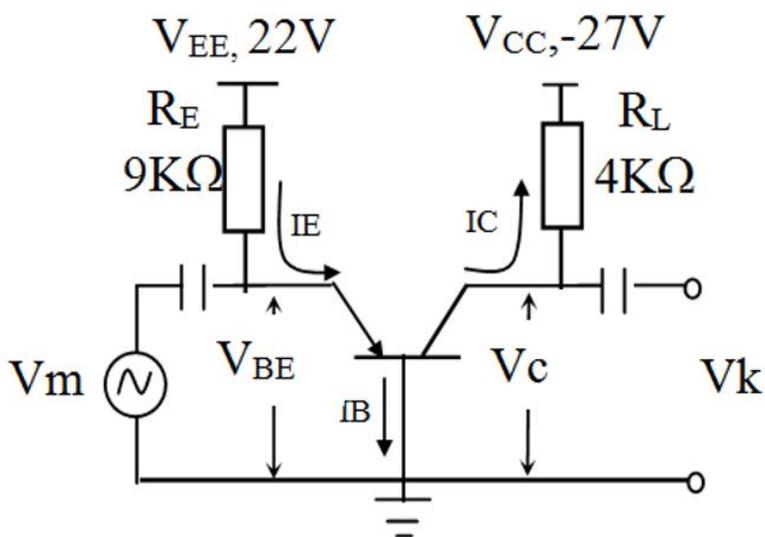
$$V_C = V_{CC} - I_C \cdot R_C$$

$$= 25\text{V} - (1\text{mA})(5\text{K})$$

$$= \underline{20\text{V}}$$

$$V_C = V_K = \underline{20\text{V}}$$

# COMMON BASE AMPLIFIER CALCULATION (E.G. 2)



- If silicon types of transistor are used. Determine the output voltage for common base amplifier above

# COMMON BASE AMPLIFIER CALCULATION (E.G. 2)

## SOLUTION

Given;

$$R_E = 9 \text{ K}\Omega, \quad R_L = 4 \text{ K}\Omega, \\ V_{EE} = 22\text{V}, \quad V_{CC} = -27\text{V}, \quad V_{BE} = 0.7\text{V}$$

### Input section

$$V_{EE} = V_{RE} + V_{BE}$$

$$V_{EE} = I_E \cdot R_E + V_{BE}$$

$$22\text{V} = I_E (9\text{K}\Omega) + 0.7\text{V}$$

$$I_E = \frac{22\text{V} - 0.7\text{V}}{9\text{K}\Omega} \\ = \underline{2.37\text{mA}}$$

### Output section

$$I_C = I_E$$

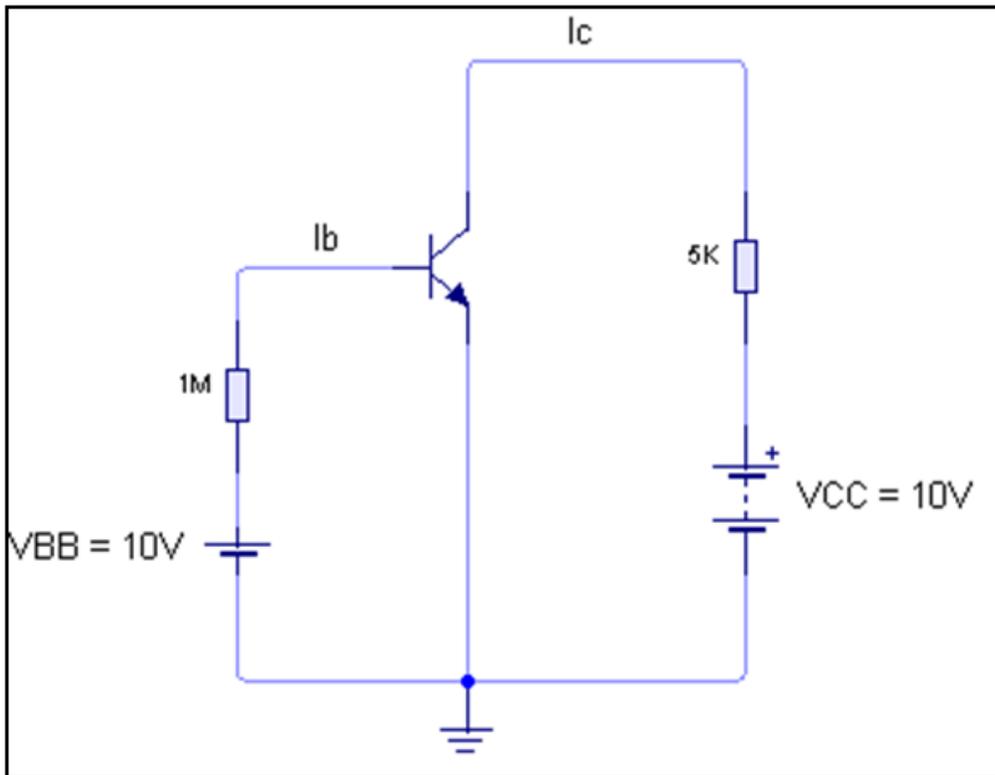
$$I_C = 2.37\text{mA}$$

$$V_{RL} = I_C \cdot R_L \\ = (2.37\text{mA})(4\text{K}\Omega) \\ = \underline{9.47\text{V}}$$

$$V_C = V_{CC} - V_{RL} \\ = 27\text{V} - 9.47\text{V} \\ = \underline{17.5\text{V}}$$

- $V_{CC} = -27\text{V}$  → In calculation, we only use the magnitude not the direction of the voltage.  
→ Thus, in calculation we only used 27V as voltage value

# COMMON EMITTER AMPLIFIER CALCULATION (E.G. 3)



Based on figure above;

- i. If  $\beta$  transistor is 100 and it is a silicon type transistor, calculate the value for  $I_c$  and  $V_C$ .
- ii. If  $\beta$  transistor is 50, disregard the value of  $V_{BE}$ , calculate the value for  $I_c$  and  $V_C$ .

# COMMON EMITTER AMPLIFIER CALCULATION (E.G. 3)

## • SOLUTION (i)

Given;

- $R_B = 1M\Omega$
- $R_L = 5 K\Omega$
- $V_{CC} = 10V$
- $V_{BB} = 10V$
- $V_{BE} = 0.7V$
- $\beta = 100$

$$V_{BB} = V_B + V_{BE}$$

$$I_B = \frac{V_{BB} - V_{BE}}{R_B}$$

$$I_B = \frac{10V - 0.7V}{1M} = 9.3\mu A$$

$$I_C = \beta \cdot I_B$$

$$I_C = 100 \times 9.3\mu$$

$$I_C = 0.93 mA$$

$$V_{CC} = V_{RL} + V_C$$

$$V_C = V_{CC} - V_{RL}$$

$$V_C = 10V - (0.93mA \times 5k\Omega)$$

$$V_C = 5.35V$$

# COMMON EMITTER AMPLIFIER CALCULATION (E.G. 3)

## • SOLUTION (ii)

Given;

- $R_B = 1M\Omega$
- $R_L = 5 K$
- $V_{CC} = 10V$
- $V_{BB} = 10V$
- $\beta = 50$

$$V_{BB} = V_B + V_{BE}$$

$$V_{BE} = 0V$$

$$I_B = \frac{V_{BB}}{R_B}$$

$$I_B = \frac{10V}{1M} = 10\mu A$$

$$I_C = \beta \cdot I_B$$

$$I_C = 50 \times 10\mu$$

$$I_C = 0.5mA$$

$$V_{CC} = V_{RL} + V_C$$

$$V_C = V_{CC} - V_{RL}$$

$$V_C = 10V - (0.5mA \times 5k\Omega)$$

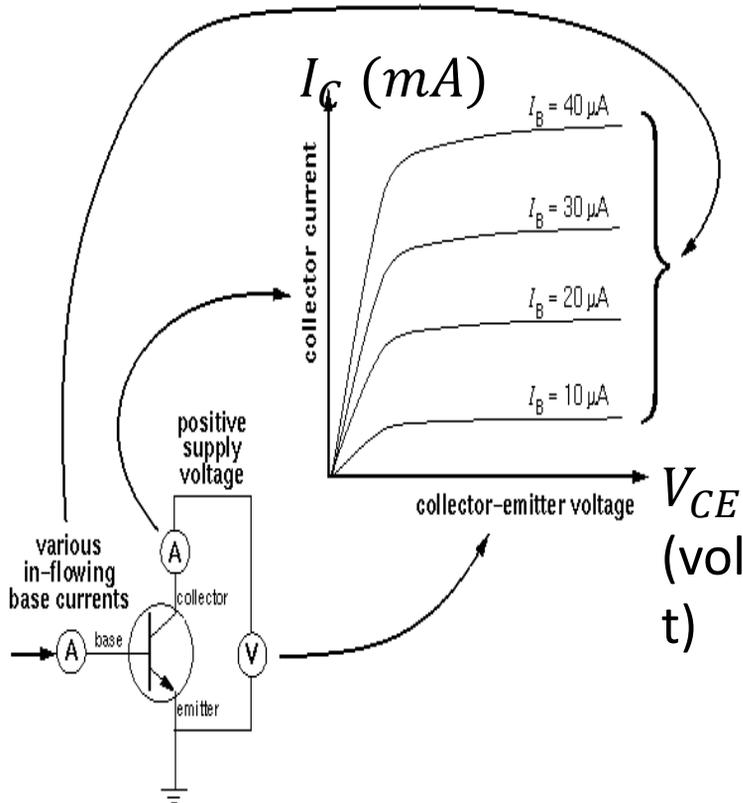
$$V_C = 7.5V$$

# COMMON EMITTER AMPLIFIER

## DC LOAD LINE

- Q POINT
- SATURATION POINT
- CUT OFF POINT

# COMMON EMITTER AMPLIFIER CHARACTERISTIC CURVES



The  $I_C - V_C$  characteristic curve is the graph of a collector current versus collector voltage that describe the output of common emitter amplifier during any changes of voltage and current

$I_B$  value proportional to forward biased voltage value  $V_{BB}$

$I_C$  value proportional to  $I_B$

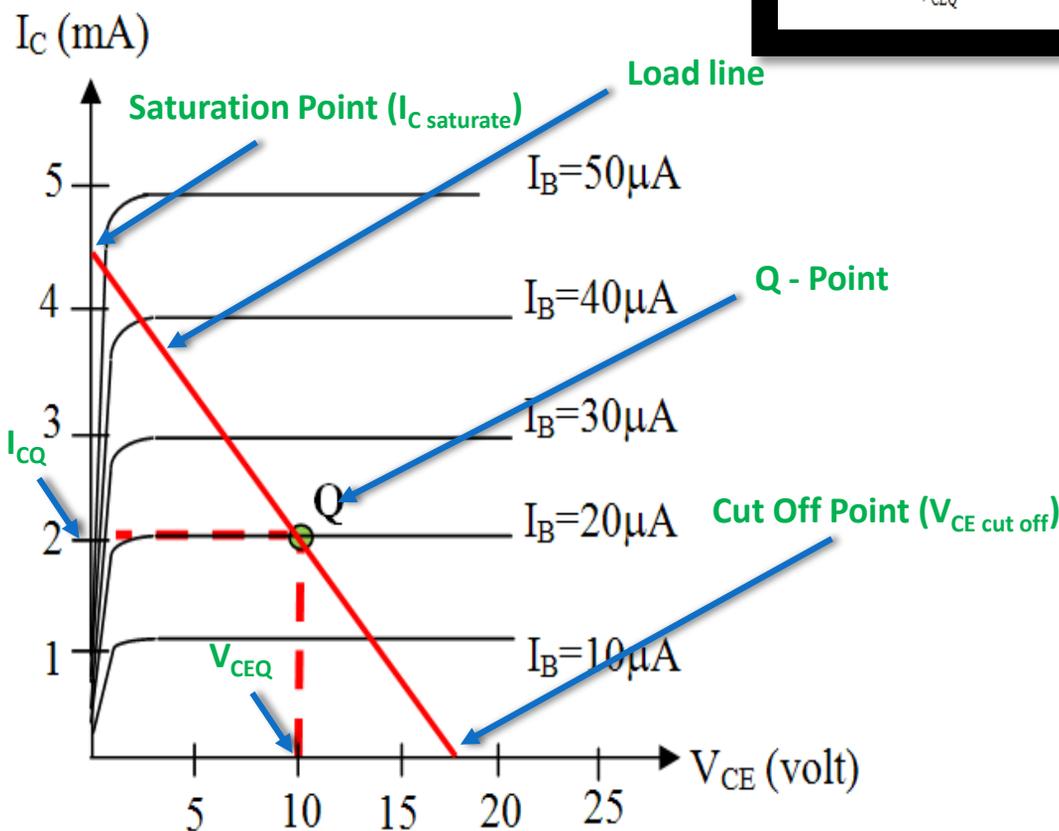
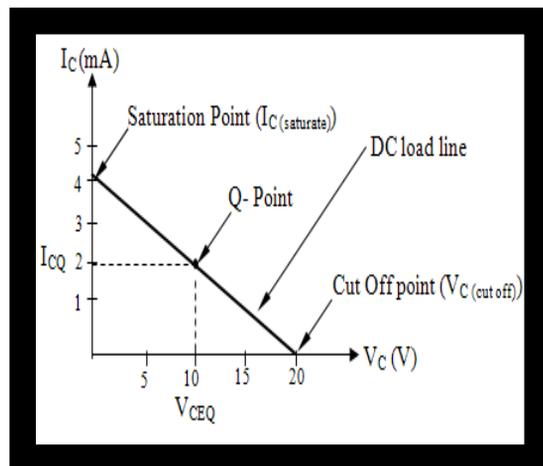
$I_C$  value is bigger (usually in mA) than to  $I_B$  (usually in  $\mu A$ )

# COMMON EMITTER AMPLIFIER

- **LOAD LINE**
  - Line connecting saturation point, Q point and cut off point.
- **Q POINT (Quiescent Point) ( $V_{CEQ}$  and  $I_{CQ}$ )**
  - Operational point is the point of intersection between  $V_{CEQ}$  and  $I_{CQ}$ .
  - $V_{CEQ}$  = voltage at operational point. ( $V_{CE} = V_{CEQ}$ )
  - $I_{CQ}$  = current at operational point. ( $I_C = I_{CQ}$ )
- **SATURATION POINT ( $I_C$  saturate)**
  - Point where the value of  $I_C$  is maximum, it's happened when there was no output voltage ( $V_C @ V_K = 0V$ ).
- **CUT OFF POINT ( $V_C$  cut off)**
  - Point where the value of  $V_C$  is maximum, it's happened when there was no output current ( $I_C = 0A$ )

# LOAD LINE, Q POINT, SATURATION POINT AND CUT OFF POINT

- DC LOAD LINE



Load line gradient depends on  $R_L$  and  $V_{CC}$  value

# LOAD LINE CALCULATION (E.G 1)

- Refer to figure below, draw the dc load line and Q point. (assume  $\beta = 100$ )

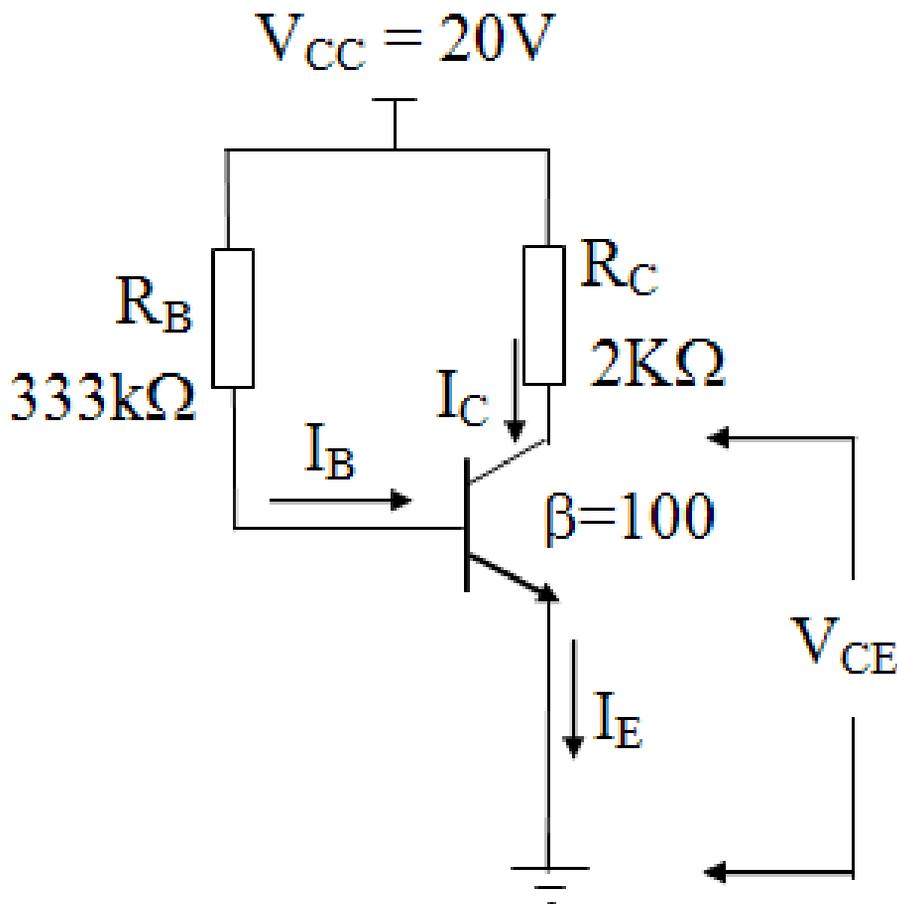


Figure : Common Emitter Amplifier Circuit

# LOAD LINE CALCULATION (E.G 1)

- SOLUTION**

$$\begin{aligned}\mapsto I_B &= \frac{V_{BB}}{R_B} \\ &= \frac{20V}{333k\Omega} \\ &= \underline{60\mu A}\end{aligned}$$

$$\begin{aligned}\mapsto I_C &= \beta \cdot I_B = (100)(60\mu A) \\ &= \underline{6mA}\end{aligned}$$

$$\begin{aligned}\mapsto V_C &= V_{CC} - I_C \cdot R_L \\ &= 20V - (6mA)(2k\Omega) \\ &= 20V - 12V \\ &= \underline{8V}\end{aligned}$$

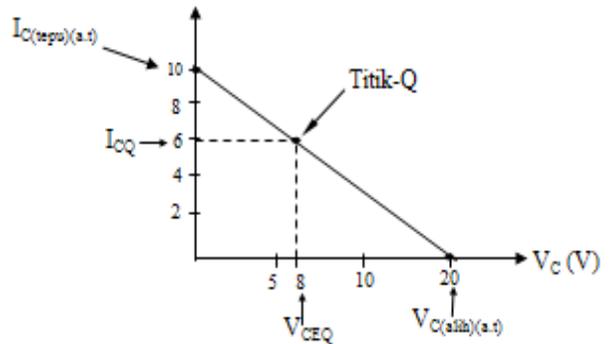
$$\Rightarrow V_{CQ} = V_C = \underline{8V}$$

$$\Rightarrow I_{CQ} = I_C = \underline{6mA}$$

$$\begin{aligned}\mapsto I_{C(\text{saturate})(dc)} &= \frac{V_{CC}}{R_L} \\ &= \underline{\underline{10mA}}\end{aligned}$$

$$\mapsto I_C = 0$$

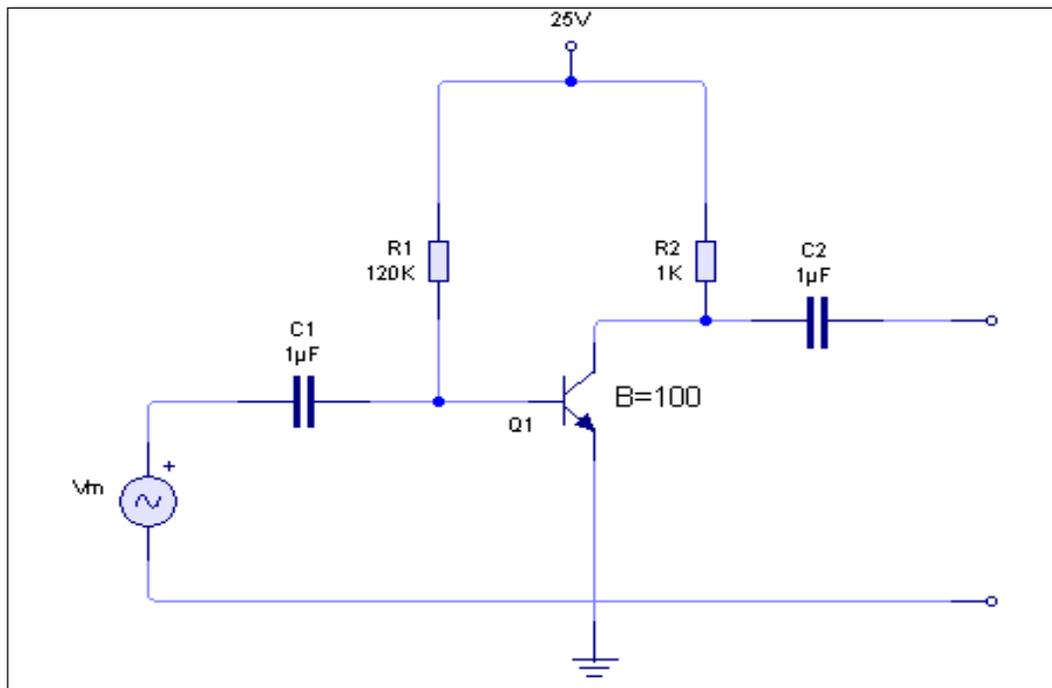
$$\mapsto V_{C(\text{cutoff})(dc)} = V_{CC} = \underline{\underline{20V}}$$



# LOAD LINE CALCULATION (E.G 2)

- Based on figure below, calculate;
  - i.  $I_c$
  - ii.  $V_c$
  - iii. AC saturation  $I_c$
  - iv. AC cut off voltage

Assume the transistor is ideal



# LOAD LINE CALCULATION (E.G 2)

- SOLUTION**

Given;

- $R_B = 120 \text{ K}\Omega$
- $R_L = 1 \text{ K}\Omega$
- $V_{CC} = 25\text{V}$
- $V_{BB} = 25\text{V}$
- $\beta = 100$

$$V_{BB} = V_B + V_{BE} \quad V_{BE} = 0\text{V}$$

$$= I_B \times R_B$$

$$I_B = \frac{V_{BB}}{R_B}$$

$$I_B = \frac{25\text{V}}{120\text{K}} = \mathbf{208.33\mu\text{A}}$$

$$I_C = \beta \cdot I_B$$

$$= 100 \times 208.33\mu$$

$$= \mathbf{20.83 \text{ mA}}$$

$$V_{CC} = V_{RL} + V_C$$

$$V_C = V_{CC} - V_{RL}$$

$$V_C = 25 \text{ V} - (20.83\text{mA} \times 1\text{k}\Omega)$$

$$V_C = \mathbf{4.167\text{V}}$$

$$I_{C(\text{saturation})} \implies V_C = 0$$

$$V_{C(\text{cut off})} \implies I_C = 0$$

$$I_{C(\text{saturation})} = \frac{V_{CC}}{R_L}$$

$$I_{C(\text{saturation})} = \frac{25\text{V}}{1\text{K}}$$

$$I_{C(\text{saturation})} = \mathbf{25\text{mA}}$$

$$V_{C(\text{cut off})} = V_{CC}$$

$$V_{C(\text{cut off})} = \mathbf{25\text{V}}$$

# COMMON EMITTER AMPLIFIER ENHANCEMENT TECHNIQUE

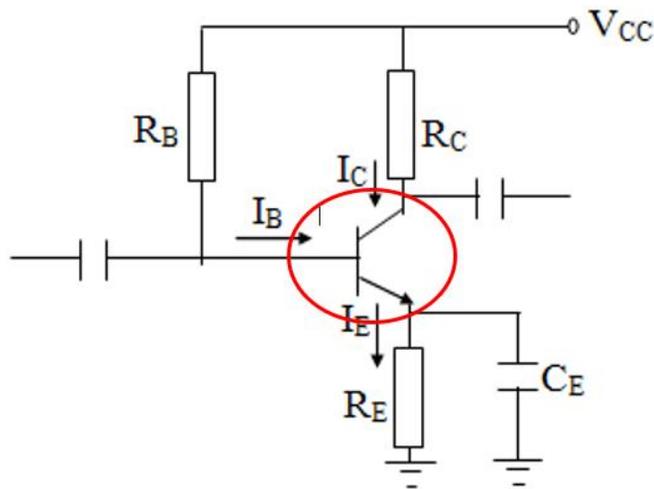
- BIASING TECHNIQUES OF COMMON EMITTER TRANSISTOR
  - BIASED VOLTAGE DIVIDER

# BIASING TECHNIQUES OF COMMON EMITTER TRANSISTOR CONFIGURATION

- $\beta$  is a gain produced by common emitter amplifier has a downside due to its relation with leakage current when the circuit temperature rises.
- To eliminate  $\beta$  weakness, stable biasing technique were introduced, which is;
  - **base biased with emitter feedback**
  - **biased voltage divider technique**

# BASE BIASED WITH EMITTER FEEDBACK

- Addition of  $R_E$  and  $C_E$  before  $I_E$  current grounded.

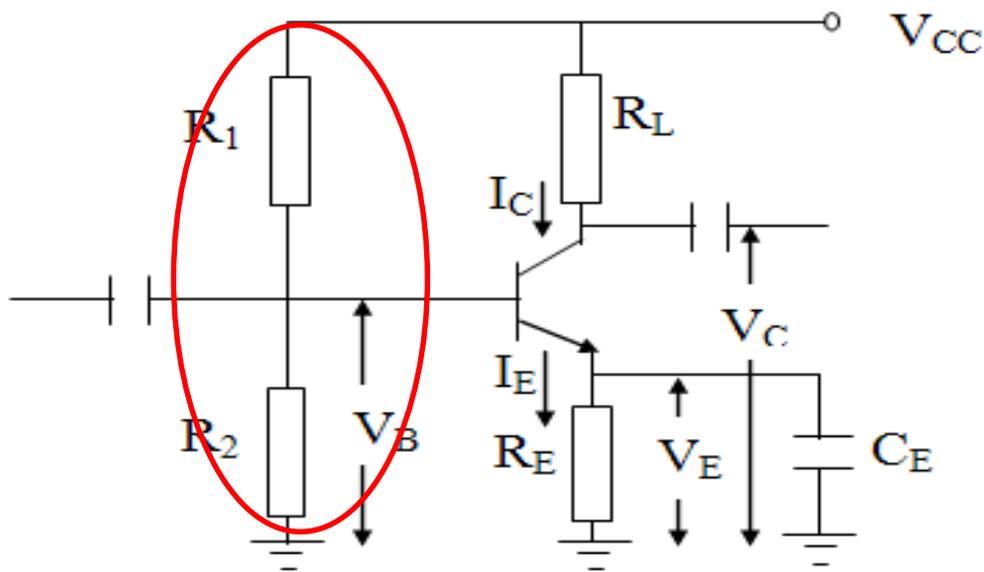


$$I_E \uparrow \quad V_{RE} \uparrow \quad V_{RB} \downarrow$$

- $R_E$  act as stabilizer for operational current (output current  $I_C$ ).
- $R_E$  will decrease the gain value due to increasing of voltage drop across the  $R_E$  resistance.
- $C_E$  act as a shunt capacitor to RE and reduce input resistance.

# BIASED VOLTAGE DIVIDER TECHNIQUE

- Addition of  $R_2$  to make a voltage divider circuit in input side of amplifier.



# FINAL EXAM QUESTIONS (1)

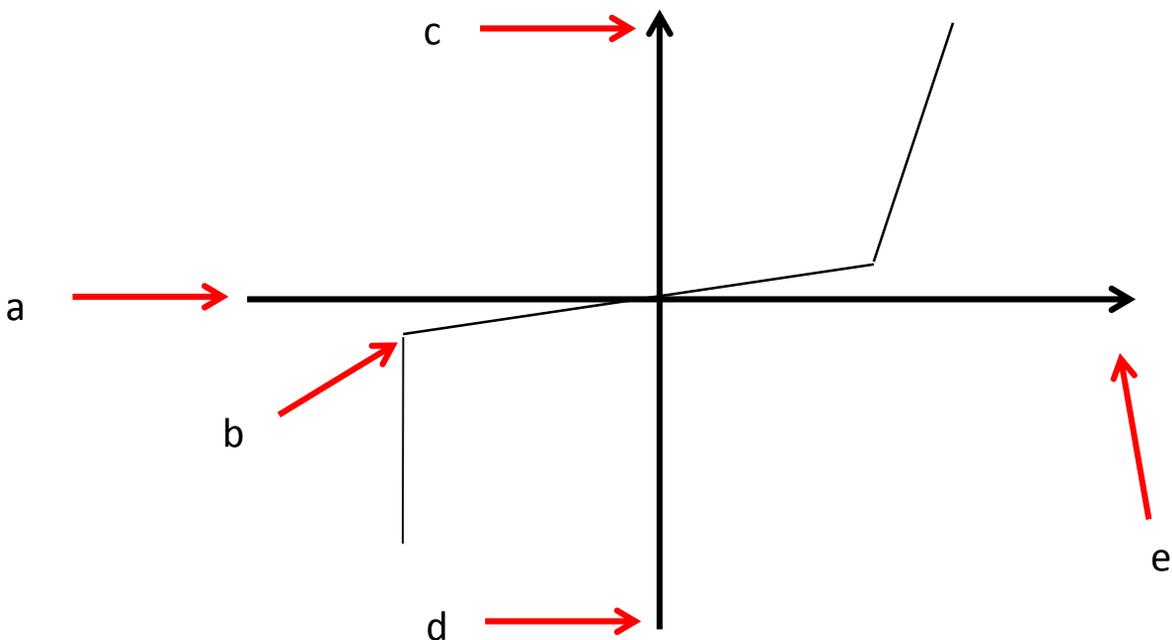
**JUNE 2014**

1. Explain the operation of ideal diode. **(3M)**
2. Explain TWO main conditions in biasing a transistor. **(6M)**
3. Explain the following terms based on the characteristic curves of SCR. **(12M)**
  - i. Forward Blocking Current
  - ii. Reverse Blocking Current
  - iii. Holding Current
  - iv. Break over Voltage
4. Differentiate between SCR and TRIAC. **(4M)**

# FINAL EXAM QUESTIONS (2)

**JUNE 2013**

1. Draw and label the schematic symbol of diode. **(1M)**
2. Explain the operation of diode when in forward bias and reverse bias. **(4M)**
3. Draw the schematic of a LED and state 3 characteristic of a LED. **(5M)**
4. Draw and label the structure and schematic symbol of transistor NPN and PNP. **(7M)**
5. Based on figure below; **(8M)**
  - i. Label the I-V characteristic curve for zener diode.
  - ii. Explain the advantages between zener diode and normal diode.



# FINAL EXAM QUESTIONS (3)

**DEC 2012**

1. Draw and label the schematic symbol of component below; **(15M)**
  - i. LED
  - ii. FET
  - iii. TRIAC
  - iv. NPN Transistor
  - v. PNP Transistor
  
2. State 3 differences between Field Effect Transistor (FET) and Bipolar Junction Transistor (BJT).  
**(6M)**
  
3. Explain the concept of ideal diode during forward bias and reverse bias. **(4M)**

# FINAL EXAM QUESTIONS (4)

## JAN 2010

1. Draw and label the symbol and structure of diode. **(2M)**
2. Sketch and label an I-V curve of silicon diode and define the following terms.
  - i. Forward current
  - ii. Reverse current
  - iii. Knee Voltage
  - iv. Breakdown voltage
  - v. Burn limit**(12M)**
3. State 2 bias conditions for transistor operation. **(2M)**
4. Transistors have 3 terminals. Describe the function of the following terminals;
  - i. Emitter
  - ii. Base
  - iii. Collector**(6M)**
5. List 3 function of SCR.  
**(3M)**

# FINAL EXAM QUESTIONS (5)

**APR 2007**

1. Draw schematic symbol of a LED.  
**(3M)**
2. Sketch and label an I-V curve of silicon diode and define the following terms.
  - i. Forward current
  - ii. Reverse current
  - iii. Breakdown voltage
  - iv. Knee voltage**(10M)**
3. State 2 bias conditions for enable a transistor to operate. **(4M)**
4. Draw a structure diagram and schematic symbol for;  
**(8M)**
  - i. transistor **NPN**
  - ii. transistor **PNP**

# FINAL EXAM QUESTIONS (6)

**JAN 2007**

1. Sketch and label an I-V curve of silicon diode and define the following terms.
  - i. Forward current
  - ii. Reverse current
  - iii. Knee Voltage
  - iv. Breakdown voltage
  - v. Burn limit

**(8M)**
2. State 3 advantages of a zener diode compared to a normal diode. **(3M)**
3. Draw the structure diagram and schematic symbol for a SCR. **(4M)**
4. State 3 method can be used to stop a SCR operation. **(6M)**
5. State 2 differences between DIAC and TRIAC. **(4M)**

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e ISBN 978-967-2241-89-8



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